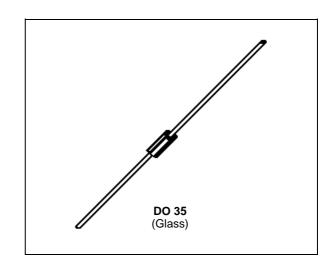
SMALL SIGNAL SCHOTTKY DIODES



DESCRIPTION

General purpose, metal to silicon diodes featuring very low turn-on voltage and fast switching.

These devices have integrated protection against excessive voltage such as electrostatic discharges.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	BAT47	BAT48	Unit	
V_{RRM}	Repetitive Peak Reverse Voltage		20	40	V
I _F	Forward Continuous Current*	T _a = 25 °C	35	mA	
I _{FRM}	Repetitive Peak Fordware Current*	1	А		
I _{FSM}	Surge non Repetitive Forward Current* $t_p = 10 \text{ms}$ 7.5				Α
		$t_p = 1s$	1.	.5	
P _{tot}	Power Dissipation* $T_a = 25 ^{\circ}\text{C}$ 330				mW
T _{stg} T _j	Storage and Junction Temperature Range - 65 to + 150 - 65 to + 125				°C
T _L	Maximum Temperature for Soldering during 10s at 4mm from Case				

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th(j-l)}	Junction-ambient*	300	°C/W

^{*} On infinite heatsink with 4mm lead length

November 1994 1/5

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	1	Min.	Тур.	Max.	Unit		
V_{BR}	$I_R = 10\mu A$		BAT47	20			V
	I _R = 25μA		BAT48	40			
V _F *	$T_j = 25^{\circ}C$ $I_F = 0.1 mA$		All Types			0.25	V
	$T_j = 25^{\circ}C$ $I_F = 1mA$					0.3	
	$T_j = 25^{\circ}C$ $I_F = 10mA$					0.4	
	$T_j = 25^{\circ}C$ $I_F = 30mA$		BAT47			0.5	
	$T_j = 25^{\circ}C$ $I_F = 150mA$					0.8	
	$T_j = 25^{\circ}C$ $I_F = 300mA$					1	
	$T_j = 25^{\circ}C$ $I_F = 50mA$		BAT48			0.5	
	$T_j = 25^{\circ}C$ $I_F = 200mA$					0.75	
	$T_j = 25^{\circ}C$ $I_F = 500mA$					0.9	
I _R *	$T_j = 25^{\circ}C$	V _R = 1.5V	All Types			1	μΑ
	$T_j = 60^{\circ}C$					10	
	$T_j = 25^{\circ}C$	V _R = 10V	BAT47			4	
	$T_j = 60^{\circ}C$					20	
	$T_j = 25^{\circ}C$	V _R = 20V				10	
	$T_j = 60^{\circ}C$					30	
	$T_j = 25^{\circ}C$	V _R = 10V	BAT48			2	
	$T_j = 60^{\circ}C$					15	
	$T_j = 25^{\circ}C$	V _R = 20V				5	
	$T_j = 60^{\circ}C$					25	
	T _j = 25°C	V _R = 40V				25	
	$T_j = 60^{\circ}C$					50	

DYNAMIC CHARACTERISTICS

Symbol		Min.	Тур.	Max.	Unit		
С	$T_j = 25^{\circ}C$ $V_R = 0V$	f = 1MHz			20		рF
	$T_j = 25^{\circ}C$ $V_R = 1V$				12		
t _{rr}	$T_j = 25^{\circ}C$ $I_F = 10mA$	$V_R = 1V$ $i_{rr} = 1mA$	$R_L = 100\Omega$		10		ns

^{*} Pulse test: $t_p\!\leq\!300\mu s$ $\delta\!<\!2\%$.



Figure 1. Forward current versus forward voltage at different temperatures (typical values).

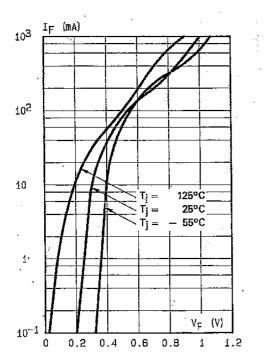


Figure 3. Reverse current versus junction temperature.

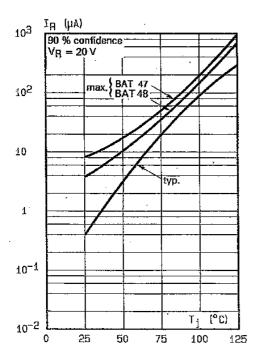


Figure 2. Forward current versus forward voltage (typical values).

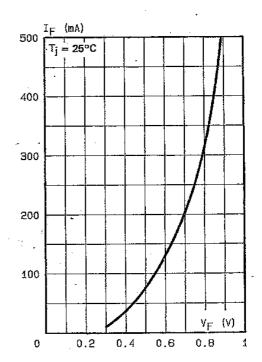


Figure 4. Reverse current versus continuous reverse voltage (typical values).

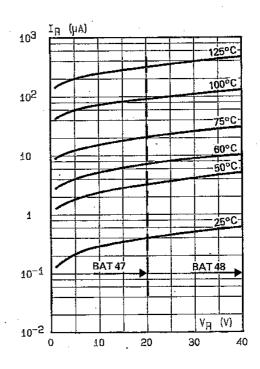
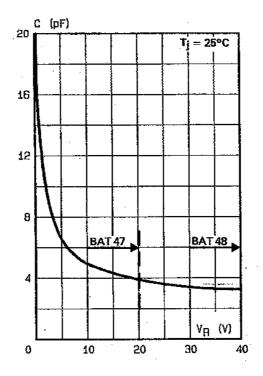
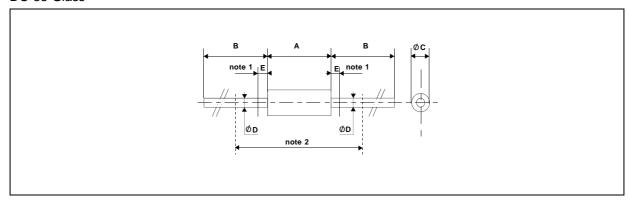


Figure 5. Capacitance C versus reverse applied voltage $V_{\mbox{\scriptsize R}}$ (typical values).



PACKAGE MECHANICAL DATA

DO 35 Glass



	DIMENSIONS					
REF.	Millimeters		illimeters Inches		NOTES	
	Min.	Max.	Min.	Max.		
Α	3.050	4.500	0.120	0.117	1 - The lead diameter Ø D is not controlled over zone E	
В	12.7		0.500		2 - The minimum axial lengh within which the device may be	
ØC	1.530	2.000	0.060	0.079	placed with its leads bent at right angles is 0.59"(15 mm)	
ØD	0.458	0.558	0.018	0.022		
Е		1.27		0.050		

Cooling method: by convection and conduction. Marking: clear, ring at cathode end. Weight: 0.015g

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsability for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

 $\hbox{@ 1994 SGS-THOMSON Microelectronics - Printed in Italy - All rights reserved.}$

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands Singapore - Spain - Sweden - Switzerland - Taiwan - United Kingdom - U.S.A.

